



N-Channel Silicon MOSFET  
**CPH3440** — General-Purpose Switching Device  
Applications

### Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

### Specifications

**Absolute Maximum Ratings** at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		20	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±10	V
Drain Current (DC)	I <sub>D</sub>		7	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	28	A
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (900mm <sup>2</sup> X0.8mm)	1.2	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

**Electrical Characteristics** at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	20			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.4		1.4	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =3.5A	6.5	10.8		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =3.5A, V <sub>GS</sub> =4V		16	22	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =1.5A, V <sub>GS</sub> =2.5V		21	29	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, f=1MHz		1305		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =10V, f=1MHz		237		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> =10V, f=1MHz		220		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		21		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit.		100		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	See specified Test Circuit.		152		ns
Fall Time	t <sub>f</sub>	See specified Test Circuit.		142		ns

Marking : ZP

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# CPH3440

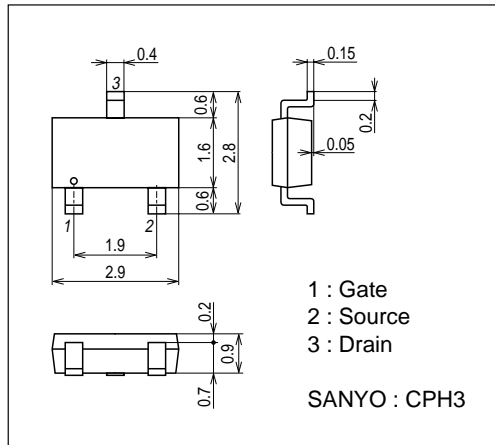
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	$V_{DS}=10V, V_{GS}=4V, I_D=7A$		17.2		nC
Gate-to-Source Charge	Qgs	$V_{DS}=10V, V_{GS}=4V, I_D=7A$		3.3		nC
Gate-to-Drain "Miller" Charge	Qgd	$V_{DS}=10V, V_{GS}=4V, I_D=7A$		5.3		nC
Diode Forward Voltage	VSD	$I_S=7A, V_{GS}=0V$		0.82	1.2	V

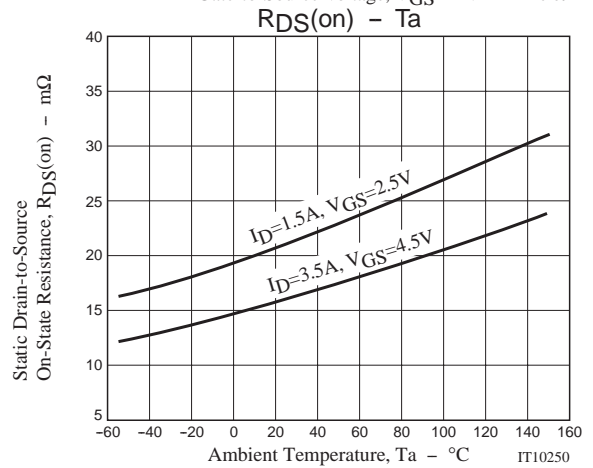
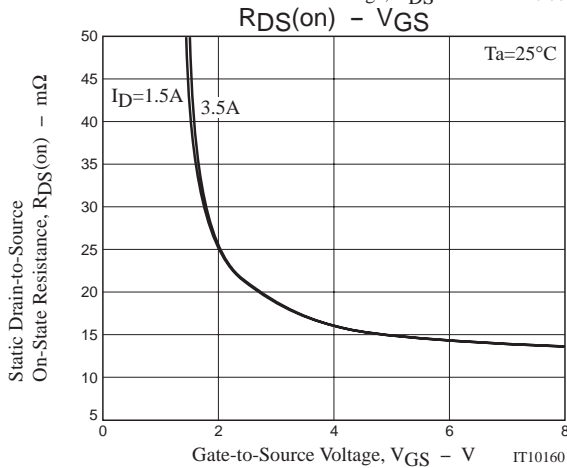
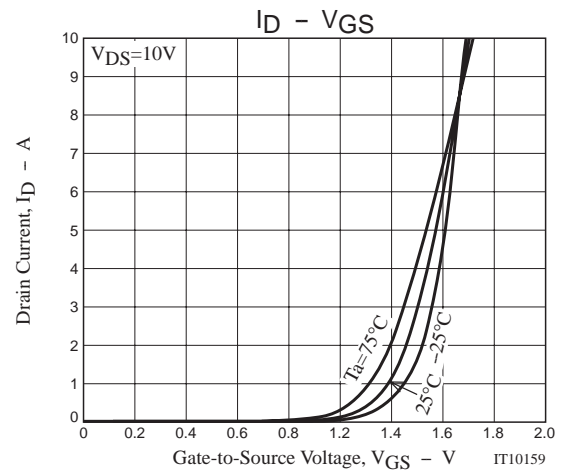
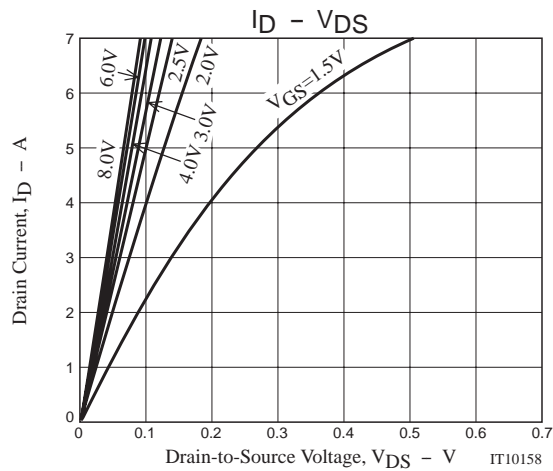
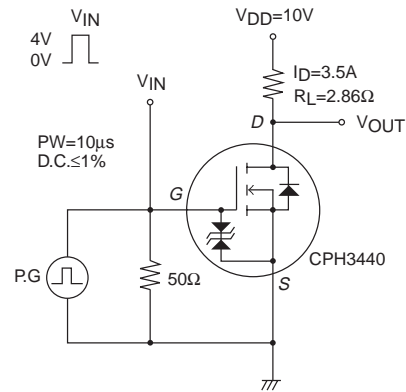
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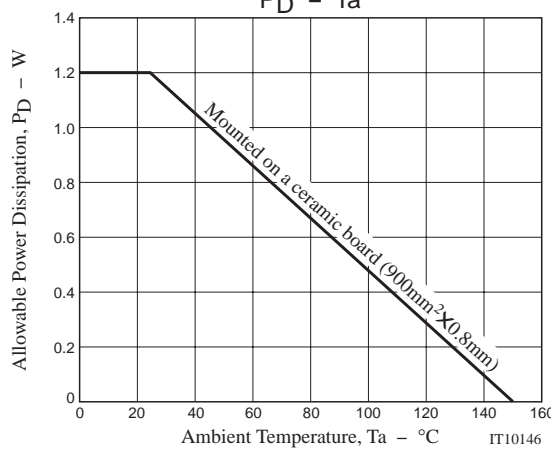
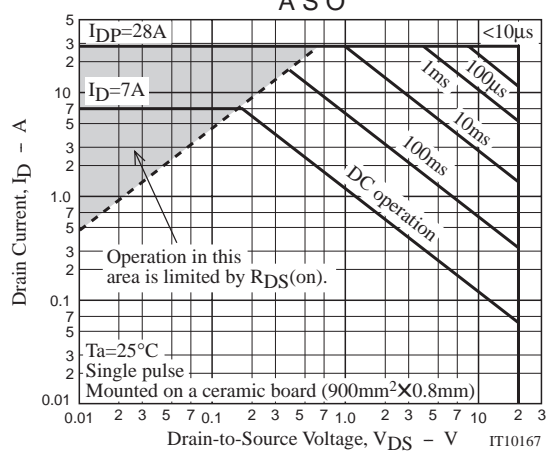
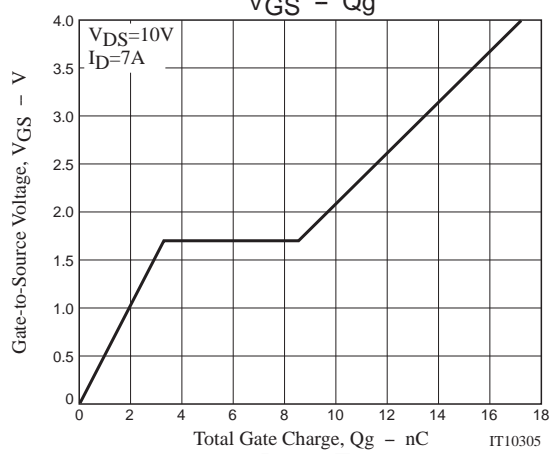
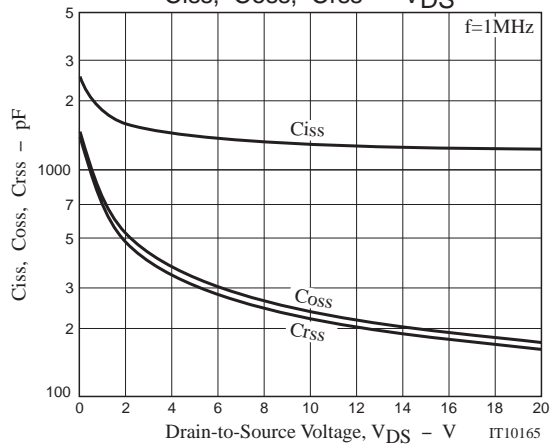
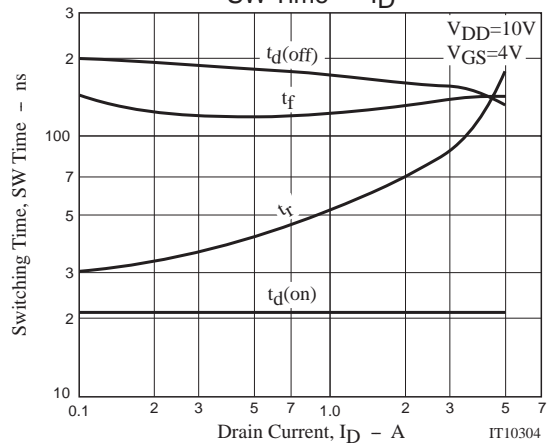
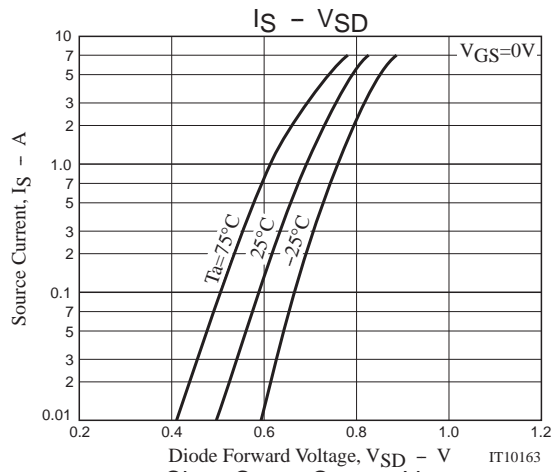
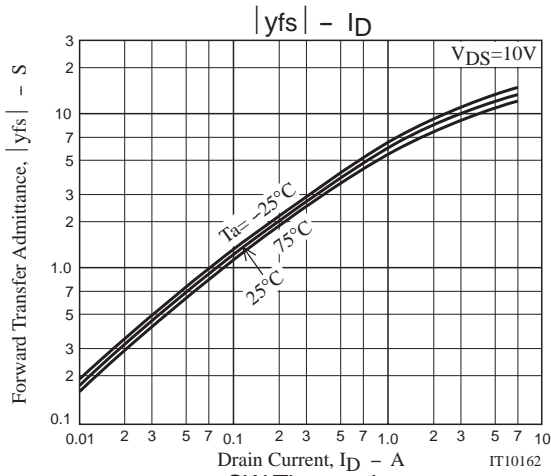
unit : mm

7015-004



## Switching Time Test Circuit





Note on usage : Since the CPH3440 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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